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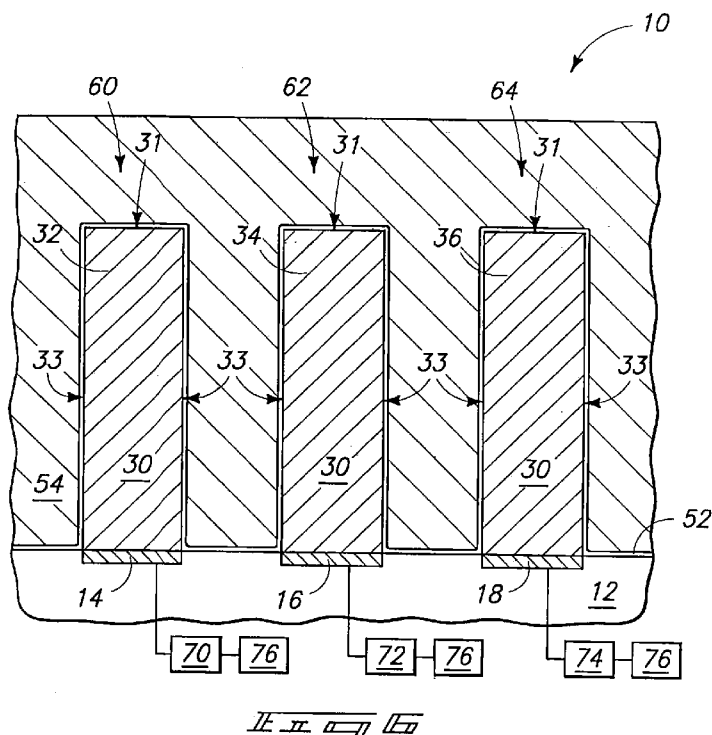
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(54) Title: METHODS OF MAKING CAPACITORS, DRAM ARRAYS AND ELECTRONIC SYSTEMS



(57) Abstract: Some embodiments include methods of making stud-type capacitors utilizing carbon-containing support material. Openings may be formed through the carbon-containing support material to electrical nodes, and subsequently conductive material may be grown within the openings. The carbon-containing support material may then be removed, and the conductive material utilized as stud-type storage nodes of stud-type capacitors. The stud-type capacitors may be incorporated into DRAM, and the DRAM may be utilized in electronic systems.

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